

PZTA92 TRANSISTOR (PNP)

FEATURES

- High Voltage Driver Applications



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-300	V
V_{CEO}	Collector-Emitter Voltage	-300	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
I_{CM}	Collector Current- Pulsed	-0.5	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	125	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1\text{mA}, I_E=0$	-300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-200\text{V}, I_E=0$			-250	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	25			
	$h_{FE(2)}$	$V_{CE}=-10\text{V}, I_C=-10\text{mA}$	40			
	$h_{FE(3)}$	$V_{CE}=-10\text{V}, I_C=-30\text{mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-20\text{mA}, I_B=-2\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-20\text{mA}, I_B=-2\text{mA}$			-0.9	V
Transition frequency	f_T	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	50			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-20\text{V}, I_E=0, f=1\text{MHz}$			6	pF

